

Version: <u>2.0</u>

Technical Specification

MODEL NO: 7.3 inch e-Paper (G)

The content of this information is subject to be changed without notice.

Customer's Confirmation

Customer

Date

Ву

Revision History

Rev.	Issued Date	Revised Contents
0.1	2020.11.18	Tentative
1.0	2021.6.30	Update 3. Mechanical Specifications
		Update 4. Mechanical Drawing of EPD Module
		Update 5. Input/Output Interface
		Update 6. Command Table
		Update 7. Electrical Characteristics
		Update 8. Optical Characteristics
		Update 10. Reliability Test
		Update 11. Block Diagram
		Update 12. Packing
		Update 13. Definition of Labels
2.0	2021.12.13	Update 4. Mechanical Drawing of EPD Module
		Update 5. Input/Output Interface
		Update 7-2) Panel DC characteristics



TECHNICAL SPECIFICATION

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1. Application

This is a reflective electrophoretic E Ink[®] Spectra[™] 3100 technology display module on an active matrix TFT substrate. The panel is capable of displaying black, white, yellow and red images depending on the associated lookup table used. The circuitry on the panel includes an integrated gate and source driver, timing controller, oscillator, DC-DC boost circuit, and memory to store the frame buffer and lookup tables, and additional circuitry to control VCOM and BORDER settings.

2. Features

- Highlight Red and Yellow color
- High contrast
- High reflectance
- Ultra wide viewing angle
- Ultra low power consumption
- Pure reflective mode
- ➢ Bi-stable
- Antiglare hard-coated front-surface
- Low current deep sleep mode
- On chip display RAM
- ➢ Waveform stored in On-chip OTP
- > Serial peripheral interface available
- > On-chip oscillator
- > On-chip booster and regulator control for generating VCOM, Gate and source driving voltage
- > I2C Signal Master Interface to read external temperature sensor
- Available in COG package

3. Mechanical Specifications

Parameter	Specifications	Unit	Remark
Screen Size	7.3	Inch	
Display Resolution	800 (H) × 480 (V)	Pixel	PPi: 127
Active Area	160 (H) × 96 (V)	mm	
Pixel Pitch	0.200 imes 0.200	mm	Square
Outline Dimension	170.2 (H) × 111.2 (V) × 0.85 (D)	mm	Without masking film
Module Weight	32.9±3.3	g	



4. Mechanical Drawing of EPD Module





5. Input/Output Interface

5-1) Connector type: FH34SRJ-50S-0.5SH(50)

Pin Assignment (50-pin)

Pin As	Pin Assignment									
Pin #	Туре	Single	Description							
1		NC	No connection and do not connect with other NC pins							
2	Р	TFT_VCOM	TFT_VCOM driving voltage							
3	Р	FPL_VCOM	FPL_VCOM driving voltage							
4		NC	NC							
5	I/O	GDRH	N-Channel MOSFET Gate Drive Control							
6	I/O	RESEH	Current Sense Input for the Control Loop							
7		GDRL	Reserved							
8	Р	GND	Ground							
9	I/O	GDRC	P-Channel MOSFET Gate Drive Control							
10	I/O	RESEC	Current Sense Input for the Control Loop							
11	Р	VPC	VPC driving voltage							
12	Р	GND	Ground							
13	Р	VGL	Negative Gate driving voltage							
14	Р	VPH	VPH driving voltage							
15	Р	VSH	Positive Source driving voltage							
16	Р	VSH_LV	Positive Source driving voltage							
17	Р	VSH_LV2	Positive Source driving voltage							
18	Р	VSL	Negative Source driving voltage							
19	Р	VSL_LV	Negative Source driving voltage							
20	Р	VSL_LV2	Negative Source driving voltage							
21	Р	GNDA	Ground ; Connect to GND							
22		REFN	Reserved							
23		REFP	Reserved							
24	0	TSCL	I2C Interface to digital temperature sensor Clock pin							
25	I/O	TSDA	I2C Interface to digital temperature sensor Data pin							
26	Ι	BS0	Bus selection pin; L: 4-wire IF. H: 3-wire IF. (Default)							
27	Ι	BS1	Bus selection pin; L: refer to BS0. (Default) H: Standard 4- wire SPI/dual SPI/quad SPI							
28	Ι	RES#	Reset							
29	0	BUSY_N	Busy state output pin							
30	Ι	D/C#	Data /Command control pin(D/C)							
31	Ι	CS#	Chip Select input pin(CSB)							



Pin #	Туре	Single	Description						
32	Ι	SCL	serial clock pin (SPI)						
33	I/O	SI0	serial data pin (SPI)						
34	I/O	SI1	serial data pin ; Reserved						
35	I/O	SI2	serial data pin ; Reserved						
36	I/O	SI3	serial data pin ; Reserved						
37	Р	VDDDO	Core logic power pin; Connect to VDDD						
38	Р	VDD	Supply voltage						
39	Р	GND	Ground; Connect to GNDA						
40	Р	VDDIO	Supply voltage						
41	Р	VCP2	Charge Pump Pin						
42	Р	CP2N	Charge Pump Pin						
43	Р	CP2P	Charge Pump Pin						
44	Р	VCP1	Charge Pump Pin						
45	Р	CP1N	Charge Pump Pin						
46	Р	CP1P	Charge Pump Pin						
47		CGH1N	Charge Pump Pin; Reserved						
48		CGH1P	Charge Pump Pin; Reserved						
49	Р	VGH	Positive Gate driving voltage						
50	Р	VCOMBD	VCOMBD driving voltage						

Note 5-1: This pin (CS#) is the chip select input connecting to the MCU. The chip is enabled for MCU communication only when CS# is pulled Low.

Note 5-2: This pin (D/C#) is Data/Command control pin connecting to the MCU. When the pin is pulled HIGH, the data will be interpreted as data. When the pin is pulled Low, the data will be interpreted as command.

Note 5-3: This pin (RES#) is reset signal input. The Reset is active Low.

Note 5-4: This pin (BUSY_N) is Busy state output pin. When Busy is low, the operation of chip should not be interrupted and any commands

should not be issued to the module. The driver IC will put Busy pin low when the driver IC is working such as:

- Outputting display waveform; or
- Programming with OTP
- Communicating with digital temperature sensor

Note 5-5: This pin (BS0) is for 3-line SPI or 4-line SPI selection. When it is "Low", 4-line SPI is selected. When it is "High", 3-line SPI (9 bits SPI) is selected. Please refer to below Table.

Table: Bus interface selection

BS0	MPU Interface
L	4-lines serial peripheral interface (SPI)
Н	3-lines serial peripheral interface (SPI) – 9 bits SPI



5-2) Panel Scan direction





6. Command Table

W/R: 0: Write cycle 1: Read cycle C/D: 0: Command 1: Data D7~D0: -: Don't care

	Command	W/R	C/D	D7	D6	D5	D4	D3	D2	D1	D0	Registers	Setting
1	Power OFF	0	0	0	0	0	0	0	0	1	0		02h
1		0	1	0	0	0	0	0	0	0	0		00h
2	Power ON	0	0	0	0	0	0	0	1	0	0		04h
2	Deer Sleen	0	0	0	0	0	0	0	1	1	1		07h
3	Deep Sleep	0	1	1	0	1	0	0	1	0	1		A5h
		0	0	0	0	0	1	0	0	0	0		10h
4	Data Start transmission	0	1	#	#	#	#	#	#	#	#		
4	Data Start transmission	0	1										
		0	1	#	#	#	#	#	#	#	#		
5	Data Dafrash	0	0	0	0	0	1	0	0	1	0		12h
5	Data Keiresn	0	1	0	0	0	0	0	0	0	1		01h



(1) Power OFF (R02H)

Action	W/R	C/D	D7	D6	D5	D4	D3	D2	D1	D0
	0	0	0	0	0	0	0	0	1	0
Power OFF	0	1	0	0	0	0	0	0	0	0

(2) Power ON (R04H)

Action	W/R	C/D	D7	D6	D5	D4	D3	D2	D1	D0
Power ON	0	0	0	0	0	0	0	1	0	0

(3) Deep Sleep (R07H)

Action	W/R	C/D	D7	D6	D5	D4	D3	D2	D1	D0
	0	0	0	0	0	0	0	1	1	1
Deep Sleep	0	1	1	0	1	0	0	1	0	1

Remark: To Exit Deep Sleep mode, User required to send HWRESET to the driver.

(4) Data Start transmission (R10H)

Action	W/R	C/D	D7	D6	D5	D4	D3	D2	D1	D0
	0	0	0	0	0	1	0	0	0	0
	0	1	#	#	#	#	#	#	#	#
Data Start transmission	0	1								
	0	1	#	#	#	#	#	#	#	#

After this command, data entries will be written into the RAM until another command is written.

(5) Data Refresh (R12H)

Action	W/R	C/D	D7	D6	D5	D4	D3	D2	D1	D0
	0	0	0	0	0	1	0	0	1	0
Data Refresh	0	1	0	0	0	0	0	0	0	1

When this command is received. IC will start the refresh process. BUSY_N will become "0". After the refresh process is finished, BUSY_N

will become "1".



7. Electrical Characteristics

7-1 Absolute Maximum Ratings:

Parameter	Symbol	Rating	Unit
Analog power	VDD	-0.5 to +3.6	V
Operating Temp. range	Topr	0 to +40	°C
Storage Temp. range	Tstg	-25 to +60	°C

Note: Maximum ratings are those values beyond which damages to the device may occur.

Functional operation should be restricted to the limits in the Electrical Characteristics chapter.



The following	The following specifications apply for: $VDD = 3.0V$, $VDD_{1.8} = 1.8V$, $TA = 25^{\circ}C$						
Symbol	Parameter	Conditions	MIN.	TYP.	MAX.	Unit	
VDD	Logic supply voltage		2.5	3.0	3.6	V	
VGH	Positive gate driving voltage		19.0	20.0	21.0	v	
VGL	Negative gate driving voltage		-21.0	-20.0	-19.0	v	
VSH	Positive source driving voltage		14.5	15.0	15.5	v	
VSL	Negative source driving voltage		-15.5	-15.0	-14.5	v	
VCOM_DC	VCOM_DC output voltage		-4.0	Adjusted	-0.3	v	
VCOM_AC	VCOM_AC output voltage		VSL+ VCOM_DC	VCOM_DC	VSH+ VCOM_DC	v	
VIL	Low level input voltage	Digital input pins		-	0.2VDD	v	
VIH	High level input voltage	Digital input pins	0.8VDD	÷	-	v	
Voh	High level output voltage	Digital output pins, IOH = 8mA	0.8VDD	-	-	v	
Vol	Low level output voltage	Digital output pins, IOL=8mA		-	0.2VDD	v	
Imstb	Module stand-by current	Shut-down		48.0		uA	
INC	Inrush Current	Booster on		64.0	84.0	mА	
Ŧ		TYP Loading Pattern		98.5	142.8	mА	
1PC	Driving Peak Current	High Loading Pattern		160.3	208.6	mA	
It com	Madala annation annat	TYP Loading Pattern	-	16.2	32.0	mА	
IMOPK	Module operating current	High Loading Pattern		59.5	86.3	mA	
р	Operation Power Dissination	TYP Loading Pattern VDD=3.0V with DC-DC		48.6	96.0	mW	
1	Speration I ower Dissipation	High Loading Pattern VDD=3.0V with DC-DC		178.5	258.9	mW	
PSTBY	Standby Power Dissipation	VDD=3.0V		144.0	44 0	uW	
IMDS	Module deep sleep current	Deep sleep mode	-	1.0	÷.	uA	

Note:

- The Inrush Current means the inrush current occurs during dual booster on sequence, and it is measured by using Oscilloscope, and extract the Max value

- The Driving Peak Current means the peak current occurs during image update after dual booster on sequence, and it is measured by using Oscilloscope, and extract the Max value.

- The Module Operating Current data is measured by using Oscilloscope, and extract the Mean value.

- The typical loading power consumption is measured using associated 25C waveform with following pattern transition: from full white pattern to color pattern. (Note 7-1)

- The high loading power consumption is measured using associated 25C waveform with following pattern



transition: from full white pattern to noise pattern (including random scattering of 4 colors) (Note 7-2)

- The minimum VDD value by 2.5V is based on typical application pattern with stable and continuing power supply. It does not apply on high loading pattern such as Note 7-2.
- The listed electrical/optical characteristics are only guaranteed under the controller & waveform provided by E Ink
- Vcom value has been set in the IC on the panel.

Note 7-1

The typical power consumption



Note 7-2

The high loading power consumption 480 (Gate)





7-3 Panel AC Characteristics

7-3-1 MCU Interface

7-3-1-1 MCU Interface Selection

In this module, there are 4-wire SPI and 3-wire SPI that can communicate with MCU. The MCU interface mode can be set by hardware

1 DCO		61 I1. 22 A Cl		:4 : - 66T?? ^	2	1.4- CDD	1 4 - 1
selection on BSU	nins when it is	HIGH 4-WIRE N	PLIS SELECTED WIT	ien il is Low -	3-wire SPL19	DUS SPLU	is selected
beleetion on DOO		ingit, i mite of		1011 IC ID DOM , .	5 mie 511()	0100 01 17	ib bereeteta.

Pin Name Data/Command Interface		Control Signal			
Bus interface	SDA	SCL	CS#	D/C#	RES#
SPI4	SDIN	SCLK	CS#	D/C#	RES#
SPI3	SDIN	SCLK	CS#	L	RES#

Table 7-1: MCU interface assignment under different bus interface mode

Note 7-3: L is connected to GND

Note 7-4: H is connected to VDD



7-3-1-2 MCU Serial Interface (4-wire SPI)

The 4-wire SPI consists of serial clock SCLK, serial data SDA, D/C#, CS#.

Function	CS#	D/C#	SCLK
Write Command	L	L	1
Write data	L	Н	1

Table 7-2: Control pins of 4-wire Serial Peripheral interface

Note 7-5: †stands for rising edge of signal

SDA is shifted into an 8-bit shift register in the order of D7, D6, ... D0. The data byte in the shift register is written to the Graphic Display Data RAM (RAM) or command register in the same clock. Under serial mode, only write operations are allowed.



Figure 7-1: Write procedure in 4-wire Serial Peripheral Interface mode



7-3-1-3 MCU Serial Interface (3-wire SPI)

The 3-wire serial interface consists of serial clock SCLK, serial data SDA and CS#.

In 3-wire SPI mode, the pin D/C# can be connected to an external ground.

The operation is similar to 4-wire serial interface while D/C# pin is not used. There are altogether 9-bits will be shifted into the shift register on every ninth clock in sequence: D/C# bit, D7 to D0 bit. The D/C# bit (first bit of the sequential data) will determine the following data byte in shift register is written to the Display Data RAM (D/C# bit = 1) or the command register (D/C# bit = 0). Under serial mode, only write operations are allowed.

Function	CS#	D/C#	SCLK
Write Command	L	Tie LOW	1
Write data	L	Tie LOW	1

Table 7-3: Control pins of 3-wire Serial Peripheral Interface

Note 7-6: †stands for rising edge of signal



Figure 7-2: Write procedure in 3-wire Serial Peripheral Interface mode



7-3-2 Timing Characteristics of Series Interface

The following specifications apply for: VDDIO - GND = 2.4V to 3.6V, TOPR = 25°C, CL=20pF

Serial Peripheral Interface Timing Characteristics

Symbol	Parameter	Min	Тур	Max	Unit
t _{css}	CSB select setup time	60			ns
t _{CSH}	CSB select hold time	65			ns
t _{scc}	CSB deselect setup time	20			ns
tснw	CSB deselect hold time	40			ns
tscycw	Serial clock cycle (Write)	50			ns
tsнw	SCL "H" pulse width (Write)	25			ns
t _{SLW}	SCL "L" pulse width (Write)	25			ns
tSCYCL	Serial clock cycle (Read)	150			ns
t _{SHR}	SCL "H" pulse width (Read)	60			ns
t _{SLR}	SCL "L" pulse width (Read)	60			ns
tsos	Data setup time	30			ns
t _{SDH}	Data hold time	30			ns
t _{ACC}	Access time			75	ns
t _{он}	Output disable time	10			ns

Note: All timings are based on 20% to 80% of VDDIO-GND





3 pin serial interface characteristics (read mode)









CSB





7-3-3) Power On/Off Characteristics

Power ON Sequence





Power OFF Sequence





8. Optical Characteristics

8-1) Specification

Measurements are made with that the illumination is under an angle of 45 degrees, the detector is perpendicular unless otherwise specified.

Symbol	Parameter	Conditions	Temperature	Min	Тур.	Max	Unit	Note
R	Reflectance	White	25°C	30	34	-	%	Note 8-1
CR	Contrast Ratio	-	25°C	10	15	-		-
RS_L*	Red State L*value	Red	25°C	23	26			Note 8-1
RS_a	Red State a* value	Red	25°C	35	39	-		Note 8-1
YS_L*	Yellow State L*value	Yellow	25°C	52	57			Note 8-1
YS_b*	Yellow State b*value	Yellow	25°C	58	66			Note 8-1
T _{update}	Update time	Red/Yellow	25°C		14		sec	
RS_L*	Red State L* value	Red	0 °C	22	26			Note 8-1
RS_a*	Red State a* value	Red	0 °C	30	35			Note 8-1
YS_L*	Yellow State L*value	Yellow	0 °C	50	56			Note 8-1
YS_b*	Yellow State b*value	Yellow	0 °C	51	60			Note 8-1
T _{update}	Update time	Red/Yellow	0 °C		40		sec	

WS: White state, DS: Dark state, RS: Red state, YS: Yellow state Note 8-1 : Luminance meter : Eye – One Pro Spectrophotometer



8-2) Definition of contrast ratio

The contrast ratio (CR) is the ratio between the reflectance in a full white area (RI) and the reflectance in x CR = RI/Rd



8-3) Reflection Ratio

The reflection ratio is expressed as ‡

 $R = Reflectance \ Factor_{white \ board} \quad x \quad (\ L_{center} \ / \ L_{white \ board})$

 L_{center} is the luminance measured at center in a white area (R=G=B=1). $L_{white board}$ is the luminance of a standard white board. Both are measured with equivalent illumination source. The viewing angle shall be no more than 2 degrees.



9. Handling, Safety and Environmental Requirements and Remark

WARNING

The display glass may break when it is dropped or bumped on a hard surface. Handle with care. Should the display break, do not touch the electrophoretic material. In case of contact with electrophoretic material, wash with water and soap.

CAUTION

The display module should not be exposed to harmful gases, such as acid and alkali gases, which corrode electronic components.

Disassembling the display module can cause permanent damage and invalidate the warranty agreements.

IPA solvent can only be applied on active area and the back of a glass. For the rest part, it is not allowed.

Mounting Precautions

(1) It's recommended that you consider the mounting structure so that uneven force (ex. Twisted stress) is not applied to the module.

(2) It's recommended that you attach a transparent protective plate to the surface in order to protect the EPD.

Transparent protective plate should have sufficient strength in order to resist external force.

(3) You should adopt radiation structure to satisfy the temperature specification.

(4) Acetic acid type and chlorine type materials for the cover case are not desirable because the former generates corrosive gas of attacking the PS at high temperature and the latter causes circuit break by electro-chemical reaction.

(5) Do not touch, push or rub the exposed PS with glass, tweezers or anything harder than HB pencil lead. And please do not rub with dust clothes with chemical treatment. Do not touch the surface of PS for bare hand or greasy cloth. (Some cosmetics deteriorate the PS)

(6) When the surface becomes dusty, please wipe gently with absorbent cotton or other soft materials like chamois soaks with petroleum benzene. Normal-hexane is recommended for cleaning the adhesives used to attach the PS. Do not use acetone, toluene and alcohol because they cause chemical damage to the PS.

(7) Wipe off saliva or water drops as soon as possible. Their long time contact with PS causes deformations and color fading.



Data sheet status						
Product specification	This data sheet contains final product specifications subjected to changes without notice.					
Limiting values						
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the						
specification is not implied. Exposure to limiting values for extended periods may affect device reliability.						

Application information

Where application information is given, it is advisory and does not form part of the specification.



10. Reliability Test TEST CONDITION REMARK 1 High Temperature Storage Ta= 60°C 40% RH, 240Hrs (Test in White pattern) 2 Low Temperature Storage Ta= -25°C, 240Hrs (Test in White pattern) High Temperature 3 Ta= 40°C 35% RH, 240Hrs Operation 4 Low Temperature Operation Ta= 0°C, 240Hrs High-Temperature, High-5 $T = +40^{\circ}C$, RH = 80%, 240Hrs Humidity Operation High Temperature, High-Ta= 60°C 80% RH, 240Hrs 6 (Test in White Pattern) Humidity Storage -25°C(30 min) ~60°C(30 min) 7 Heat Shock (Test in White pattern) 50 cycle, 1Hr/cycle (Machine model) +/- 200V 8 Electrostatic Discharge Non-operation 0Ω, 200pF

Actual EMC level to be measured on customer application.

Note: The protective film must be removed before temperature test.

< Criteria >

In the standard conditions, there is not display function NG issue occurred. All the cosmetic specification is judged before the reliability stress.



11. Block Diagram

